

**Type 2N6193**  
**Geometry 9700**  
**Polarity PNP**  
**Qual Level: JAN - JANTXV**

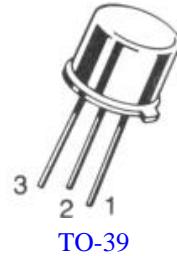
**Generic Part Number:**  
**2N6193**

**REF: MIL-PRF-19500/561**

**Features:**

- Silicon transistor for use in switching applications.
- Housed in a [TO-39](#) case.
- Also available in chip form using the [9700](#) chip geometry.
- The Min and Max limits shown are per [MIL-PRF-19500/561](#) which Semicoa meets in all cases.

[\*\*Request Quotation\*\*](#)



**Maximum Ratings**

$T_C = 25^\circ\text{C}$  unless otherwise specified

Rating	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	100	V
Collector-Base Voltage	$V_{CBO}$	100	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current, Continuous	$I_C$	5.0	A
Base Current, Continuous	$I_B$	1.0	A
Power Dissipation $T_A = 25^\circ\text{C}$ ambient Derate above $25^\circ\text{C}$	$P_T$	1.0 5.71	W $\text{mW}^\circ\text{C}$
Power Dissipation $T_A = 25^\circ\text{C}$ ambient Derate above $25^\circ\text{C}$	$P_T$	10.0 57.1	Watt $\text{mW}^\circ\text{C}$
Operating Junction Temperature	$T_J$	-55 to +200	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 to +200	$^\circ\text{C}$

### Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise specified

OFF Characteristics	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage $I_C = 50 \text{ mA, pulsed}$	$V_{(\text{BR})\text{CEO}}$	100	---	V
Collector-Base Cutoff Current $V_{CB} = 100 \text{ V}$	$I_{CBO}$	---	10	$\mu\text{A}$
Base-Emitter Cutoff Current $V_{EB} = 6 \text{ V}$ $V_{EB} = 5.5 \text{ V, } I_C = 0$	$I_{EBO}$ $I_{EBO2}$	---	100 1.0	$\mu\text{A}$ mA
Collector-Emitter Cutoff Current $V_{CE} = 100 \text{ V}$ $V_{CE} = 90 \text{ V, } V_{BE} = 1.5 \text{ V}$ $V_{CE} = 90 \text{ V, } V_{BE} = 1.5 \text{ V, } T_A = +150^\circ\text{C}$	$I_{CEO}$ $I_{CEX1}$ $I_{CEX2}$	---	100 10 1.0	$\mu\text{A}$ $\mu\text{A}$ mA

ON Characteristics	Symbol	Min	Max	Unit
<b>Forward Current Transfer Ratio</b> $I_C = 0.5 \text{ A, } V_{CE} = 2.0 \text{ V, pulsed}$ $I_C = 2.0 \text{ A, } V_{CE} = 2.0 \text{ V, pulsed}$ $I_C = 5.0 \text{ A, } V_{CE} = 2.0 \text{ V, pulsed}$ $I_C = 2.0 \text{ A, } V_{CE} = 2.0 \text{ V pulsed, } T_C = -55^\circ\text{C}$	$h_{FE1}$ $h_{FE2}$ $h_{FE3}$ $h_{FE4}$	60 60 40 12	---	---
<b>Base-Emitter Saturation Voltage</b> $I_C = 2.0 \text{ A, } I_B = 0.2 \text{ A, pulsed}$ $I_C = 5.0 \text{ A, } I_B = 0.5 \text{ A, pulsed}$	$V_{BE(\text{sat})1}$ $V_{BE(\text{sat})2}$	---	1.2 1.8	V dc V dc
<b>Collector-Emitter Saturation Voltage</b> $I_C = 2.0 \text{ A, } I_B = 0.2 \text{ A, pulsed}$ $I_C = 5.0 \text{ A, } I_B = 0.5 \text{ A, pulsed}$	$V_{CE(\text{sat})1}$ $V_{CE(\text{sat})2}$	---	0.7 1.2	V dc V dc

Small Signal Characteristics	Symbol	Min	Max	Unit
Magnitude of Common Emitter Small Signal Short Circuit Forward Current Transfer Ratio $V_{CE} = 5 \text{ V, } I_C = 0.5 \text{ A, } f = 10 \text{ MHz}$	$ h_{fe} $	3.0	15	---
Input Capacitance, Output Open Circuited $V_{CB} = 10 \text{ V, } I_E = 0, 100 \text{ kHz} < f < 1 \text{ MHz}$	$C_{IBO}$	---	1250	pF
Open Circuit Output Capacitance $V_{CB} = 10 \text{ V, } I_E = 0, 100 \text{ kHz} < f < 1 \text{ MHz}$	$C_{OBO}$	---	300	pF

Switching Time	Symbol	Min	Max	Unit
Delay Time Per figure 5, MIL-PRF-19500/561B	$t_d$	---	100	ns
Rise Time Per figure 5, MIL-PRF-19500/561B	$t_r$	---	100	ns
Storage Time Per figure 5, MIL-PRF-19500/561B	$t_s$	---	2	ns
Fall Time Per figure 5, MIL-PRF-19500/561B	$t_f$	---	200	ns